

## N - CHANNEL ENHANCEMENT MODE " SINGLE FEATURE SIZE™ " POWER MOSFET

| TYPE      | V <sub>DSS</sub> | R <sub>DS(on)</sub> | I <sub>D</sub> |
|-----------|------------------|---------------------|----------------|
| STB50NE08 | 80 V             | <0.024 Ω            | 50 A           |

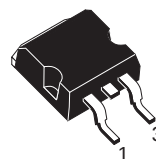
- TYPICAL R<sub>DS(on)</sub> = 0.020 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW GATE CHARGE AT 100 °C
- APPLICATION ORIENTED CHARACTERIZATION
- FOR THROUGH-HOLE VERSION CONTACT SALES OFFICE

### DESCRIPTION

This Power MOSFET is the latest development of SGS-THOMSON unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

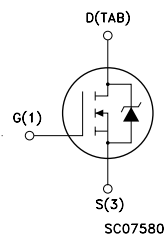
### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC & DC-AC CONVERTERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)



**D²PAK  
TO-263**  
(suffix "T4")

### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

| Symbol              | Parameter                                             | Value      | Unit |
|---------------------|-------------------------------------------------------|------------|------|
| V <sub>DS</sub>     | Drain-source Voltage (V <sub>GS</sub> = 0)            | 80         | V    |
| V <sub>DGR</sub>    | Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)         | 80         | V    |
| V <sub>GS</sub>     | Gate-source Voltage                                   | ± 20       | V    |
| I <sub>D</sub>      | Drain Current (continuous) at T <sub>c</sub> = 25 °C  | 50         | A    |
| I <sub>D</sub>      | Drain Current (continuous) at T <sub>c</sub> = 100 °C | 35         | A    |
| I <sub>DM</sub> (•) | Drain Current (pulsed)                                | 200        | A    |
| P <sub>tot</sub>    | Total Dissipation at T <sub>c</sub> = 25 °C           | 150        | W    |
|                     | Derating Factor                                       | 1          | W/°C |
| dv/dt (1)           | Peak Diode Recovery voltage slope                     | 6          | V/ns |
| T <sub>stg</sub>    | Storage Temperature                                   | -65 to 175 | °C   |
| T <sub>j</sub>      | Max. Operating Junction Temperature                   | 175        | °C   |

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 50 A, di/dt ≤ 300 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

## THERMAL DATA

|                       |                                                |     |      |      |
|-----------------------|------------------------------------------------|-----|------|------|
| R <sub>thj-case</sub> | Thermal Resistance Junction-case               | Max | 1    | °C/W |
| R <sub>thj-amb</sub>  | Thermal Resistance Junction-ambient            | Max | 62.5 | °C/W |
| R <sub>thc-sink</sub> | Thermal Resistance Case-sink                   | Typ | 0.5  | °C/W |
| T <sub>l</sub>        | Maximum Lead Temperature For Soldering Purpose |     | 300  | °C   |

## AVALANCHE CHARACTERISTICS

| Symbol          | Parameter                                                                                                                  | Max Value | Unit |
|-----------------|----------------------------------------------------------------------------------------------------------------------------|-----------|------|
| I <sub>AR</sub> | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)                        | 50        | A    |
| E <sub>AS</sub> | Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V) | 300       | mJ   |

ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

## OFF

| Symbol               | Parameter                                             | Test Conditions                                                                      | Min. | Typ. | Max.    | Unit     |
|----------------------|-------------------------------------------------------|--------------------------------------------------------------------------------------|------|------|---------|----------|
| V <sub>(BR)DSS</sub> | Drain-source Breakdown Voltage                        | I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0                                          | 80   |      |         | V        |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0) | V <sub>DS</sub> = Max Rating<br>V <sub>DS</sub> = Max Rating T <sub>c</sub> = 125 °C |      |      | 1<br>10 | μA<br>μA |
| I <sub>GSS</sub>     | Gate-body Leakage Current (V <sub>DS</sub> = 0)       | V <sub>GS</sub> = ± 20 V                                                             |      |      | ± 100   | nA       |

## ON (\*)

| Symbol              | Parameter                         | Test Conditions                                                                         | Min. | Typ.  | Max.  | Unit |
|---------------------|-----------------------------------|-----------------------------------------------------------------------------------------|------|-------|-------|------|
| V <sub>GS(th)</sub> | Gate Threshold Voltage            | V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA                               | 2    | 3     | 4     | V    |
| R <sub>DS(on)</sub> | Static Drain-source On Resistance | V <sub>GS</sub> = 10V I <sub>D</sub> = 25 A                                             |      | 0.020 | 0.024 | mΩ   |
| I <sub>D(on)</sub>  | On State Drain Current            | V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub><br>V <sub>GS</sub> = 10 V | 50   |       |       | A    |

## DYNAMIC

| Symbol              | Parameter                    | Test Conditions                                                                     | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|-------------------------------------------------------------------------------------|------|------|------|------|
| g <sub>fs</sub> (*) | Forward Transconductance     | V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> I <sub>D</sub> = 25 A | 20   | 35   |      | S    |
| C <sub>iss</sub>    | Input Capacitance            | V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0                                |      | 3850 | 5100 | pF   |
| C <sub>oss</sub>    | Output Capacitance           |                                                                                     |      | 480  | 650  | pF   |
| C <sub>rss</sub>    | Reverse Transfer Capacitance |                                                                                     |      | 105  | 140  | pF   |

**ELECTRICAL CHARACTERISTICS** (continued)**SWITCHING ON**

| Symbol      | Parameter          | Test Conditions                                                            | Min. | Typ. | Max. | Unit |
|-------------|--------------------|----------------------------------------------------------------------------|------|------|------|------|
| $t_{d(on)}$ | Turn-on Time       | $V_{DD} = 40\text{ V}$ $I_D = 25\text{ A}$                                 |      | 37   | 50   | ns   |
| $t_r$       | Rise Time          | $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$<br>(see test circuit, figure 3) |      | 95   | 130  | ns   |
| $Q_g$       | Total Gate Charge  | $V_{DD} = 64\text{ V}$ $I_D = 50\text{ A}$ $V_{GS} = 10\text{ V}$          |      | 85   | 110  | nC   |
| $Q_{gs}$    | Gate-Source Charge |                                                                            |      | 19   |      | nC   |
| $Q_{gd}$    | Gate-Drain Charge  |                                                                            |      | 28   |      | nC   |

**SWITCHING OFF**

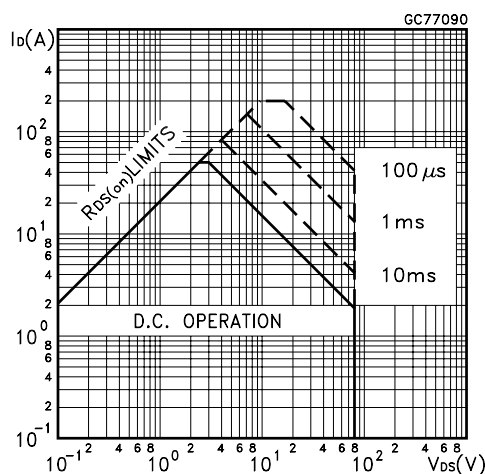
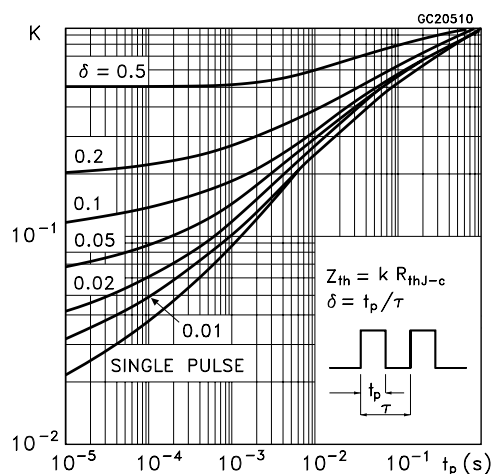
| Symbol        | Parameter             | Test Conditions                                                            | Min. | Typ. | Max. | Unit |
|---------------|-----------------------|----------------------------------------------------------------------------|------|------|------|------|
| $t_{r(Voff)}$ | Off-voltage Rise Time | $V_{DD} = 64\text{ V}$ $I_D = 50\text{ A}$                                 |      | 12   | 17   | ns   |
| $t_f$         | Fall Time             | $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$<br>(see test circuit, figure 5) |      | 30   | 40   | ns   |
| $t_c$         | Cross-over Time       |                                                                            |      | 50   | 68   | ns   |

**SOURCE DRAIN DIODE**

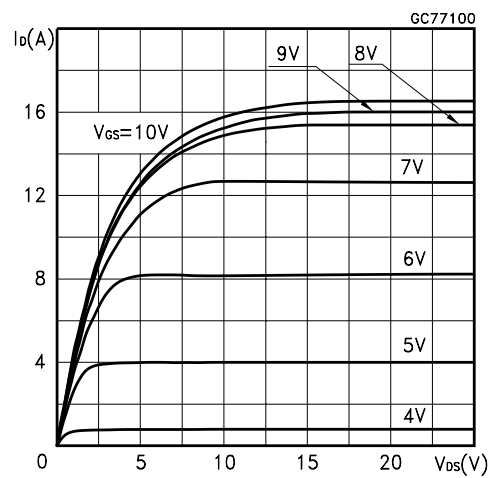
| Symbol             | Parameter                     | Test Conditions                                                                                                                                       | Min. | Typ. | Max. | Unit |
|--------------------|-------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| $I_{SD}$           | Source-drain Current          |                                                                                                                                                       |      |      | 50   | A    |
| $I_{SDM(\bullet)}$ | Source-drain Current (pulsed) |                                                                                                                                                       |      |      | 200  | A    |
| $V_{SD} (*)$       | Forward On Voltage            | $I_{SD} = 50\text{ A}$ $V_{GS} = 0$                                                                                                                   |      |      | 1.5  | V    |
| $t_{rr}$           | Reverse Recovery Time         | $I_{SD} = 50\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$<br>$V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$<br>(see test circuit, figure 5) |      | 100  |      | ns   |
| $Q_{rr}$           | Reverse Recovery Charge       |                                                                                                                                                       |      | 400  |      | nC   |
| $I_{RRM}$          | Reverse Recovery Current      |                                                                                                                                                       |      | 8    |      | A    |

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

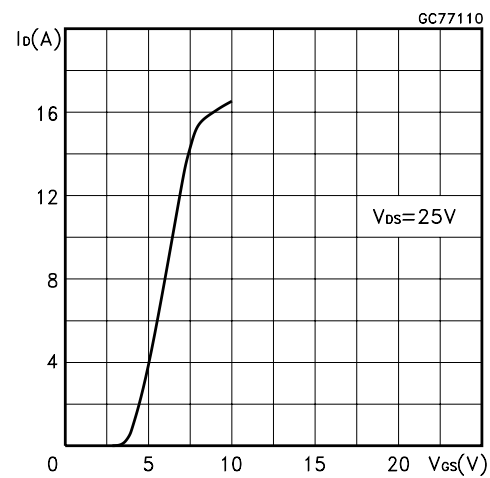
(•) Pulse width limited by safe operating area

**Safe Operating Area****Thermal Impedance**

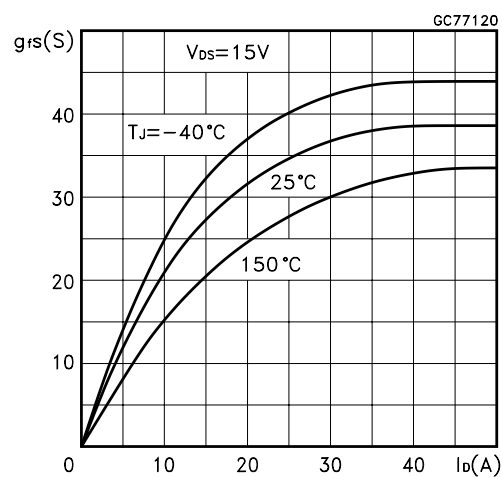
Output Characteristics



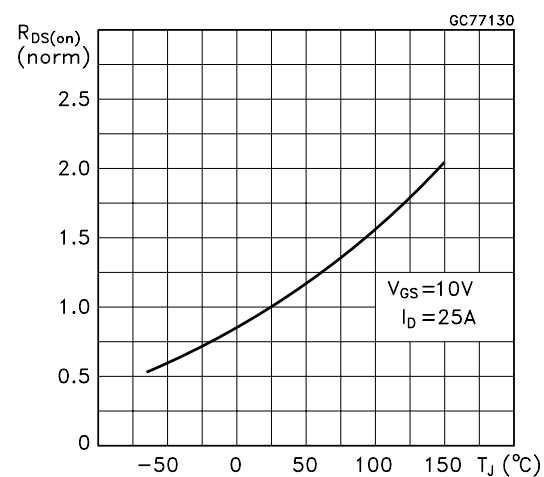
Transfer Characteristics



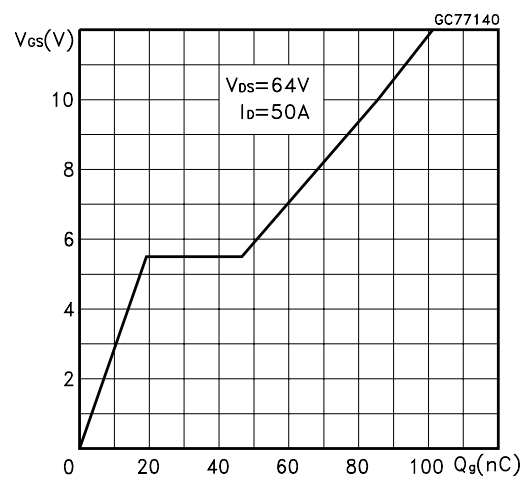
Transconductance



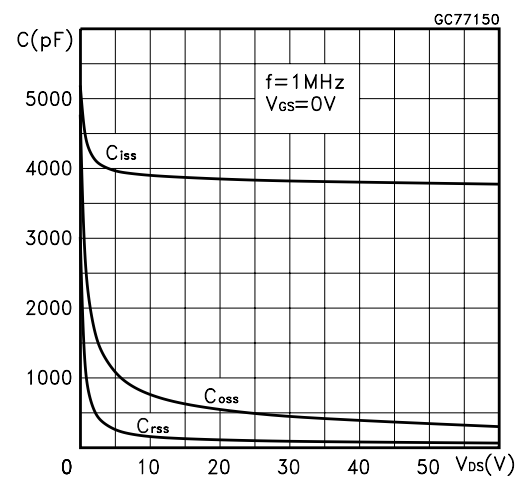
Static Drain-source On Resistance



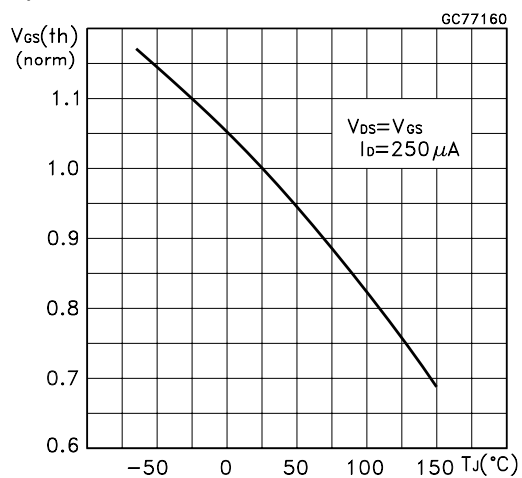
Gate Charge vs Gate-source Voltage



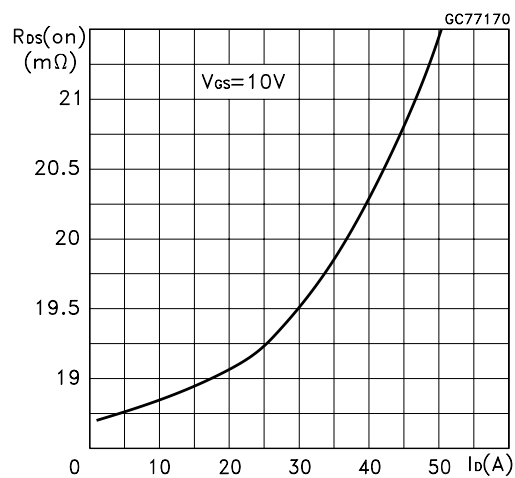
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

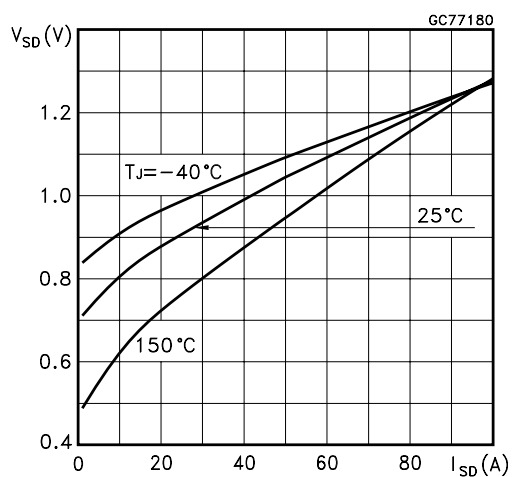


Fig. 1: Unclamped Inductive Load Test Circuit

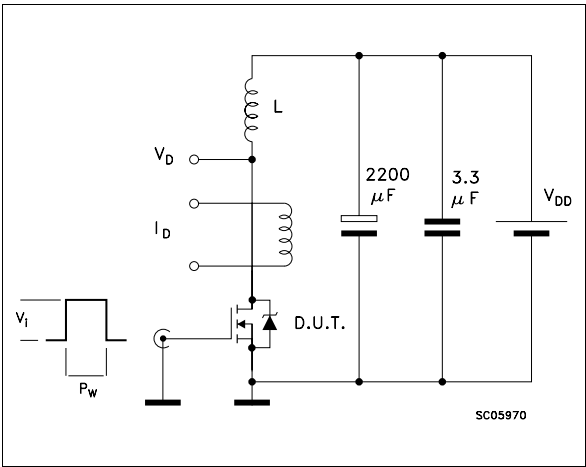


Fig. 2: Unclamped Inductive Waveform

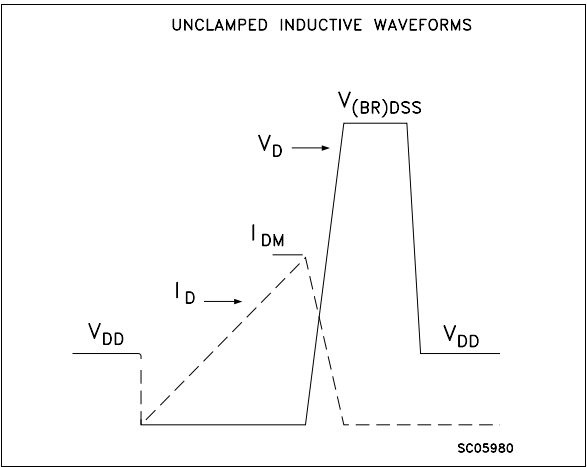


Fig. 3: Switching Times Test Circuits For Resistive Load

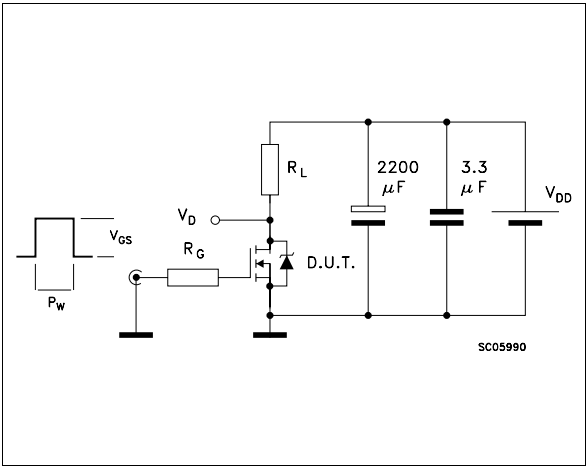


Fig. 4: Gate Charge test Circuit

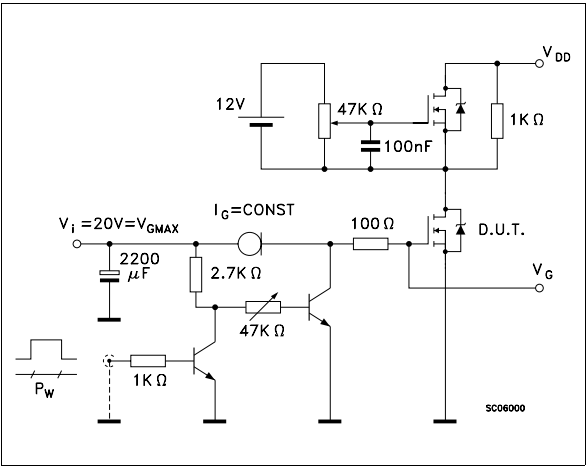
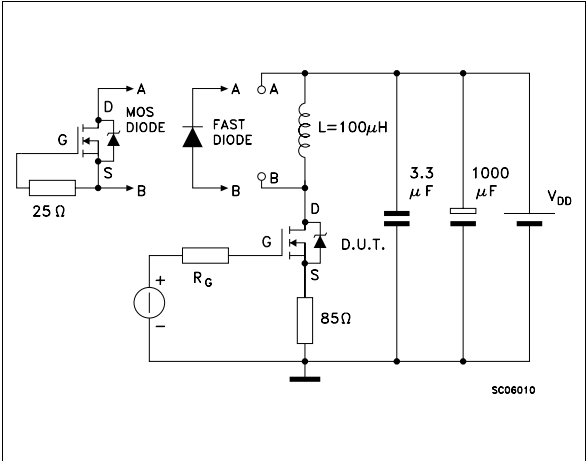
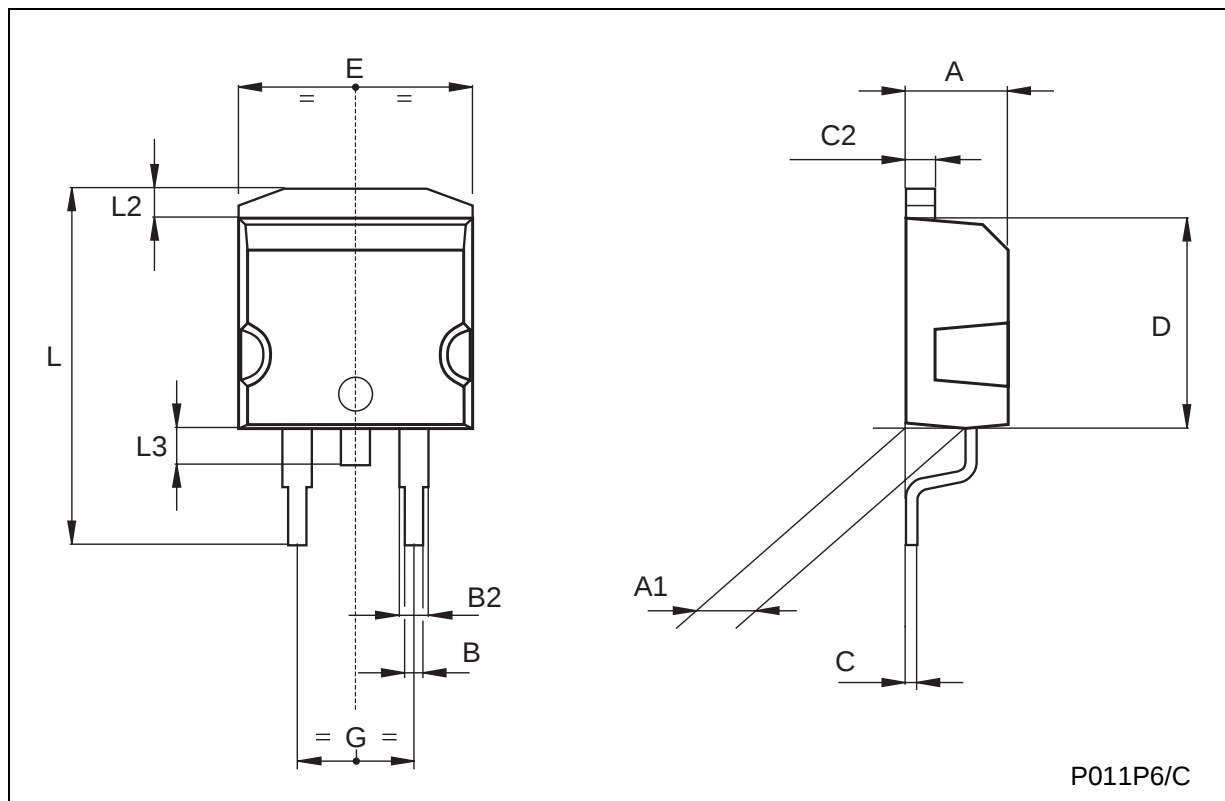


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-263 (D<sup>2</sup>PAK) MECHANICAL DATA

| DIM. | mm   |      |       | inch  |      |       |
|------|------|------|-------|-------|------|-------|
|      | MIN. | TYP. | MAX.  | MIN.  | TYP. | MAX.  |
| A    | 4.3  |      | 4.6   | 0.169 |      | 0.181 |
| A1   | 2.49 |      | 2.69  | 0.098 |      | 0.106 |
| B    | 0.7  |      | 0.93  | 0.027 |      | 0.036 |
| B2   | 1.25 |      | 1.4   | 0.049 |      | 0.055 |
| C    | 0.45 |      | 0.6   | 0.017 |      | 0.023 |
| C2   | 1.21 |      | 1.36  | 0.047 |      | 0.053 |
| D    | 8.95 |      | 9.35  | 0.352 |      | 0.368 |
| E    | 10   |      | 10.28 | 0.393 |      | 0.404 |
| G    | 4.88 |      | 5.28  | 0.192 |      | 0.208 |
| L    | 15   |      | 15.85 | 0.590 |      | 0.624 |
| L2   | 1.27 |      | 1.4   | 0.050 |      | 0.055 |
| L3   | 1.4  |      | 1.75  | 0.055 |      | 0.068 |



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